REVISION HISTORY

Revision	Description	Issue Date
Rev. 1.0	Initial Issue	June.2014

AS7C38096B

1024K X 8 BIT HIGH SPEED CMOS SRAM

FEATURES

- Fast access time : 10ns
- **Low power consumption:**
  Operating current:
  90/80mA (TYP.)
  Standby current:
  3mA (TYP.)
- Single 3.3V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage: 1.5V (MIN.)
- **All parts are ROHS Compliant**
- Package : 48-ball 6mm x 8mm TFBGA

GENERAL DESCRIPTION

The AS7C38096B is a 16M-bit high speed CMOS static random access memory organized as 1,024K words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The AS7C38096B operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

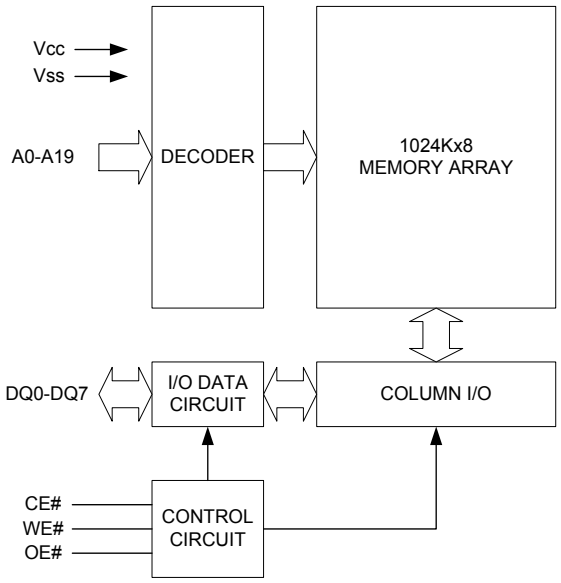
Table 1. Speed Grade Information

Product Family	V_{CC} Range	Speed	Power Dissipation	
			Standby(I_{SB1},TYP.)	Operating(I_{CC},TYP.)
AS7C38096B	2.7 ~ 3.6V	10ns	3mA	80mA

Table 2. Ordering Information

Product part No	Org	Temperature	Package
AS7C38096B-10BIN	1024K x 8	Industrial -40°C to 85°C	48-ball 6mm x 8mm TFBGA

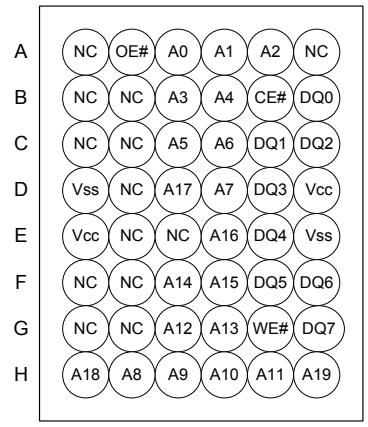
FUNCTIONAL BLOCK DIAGRAM



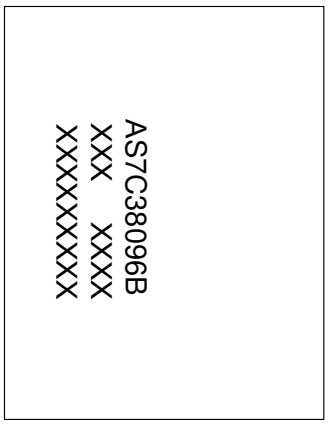
PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 – A19	Address Inputs
DQ0 – DQ7	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
V_{CC}	Power Supply
V_{SS}	Ground

PIN CONFIGURATION



TFBGA(See through with Top View)



TFBGA(Top View)

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V_{CC} relative to V_{SS}	V_{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to V_{SS}	V_{T2}	-0.5 to Vcc+0.5	V
Operating Temperature	T_A	-40 to 85(I grade)	℃
Storage Temperature	T_{STG}	-65 to 150	℃
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA

*Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High-Z	I_{SB1}
Output Disable	L	H	H	High-Z	I_{CC}
Read	L	L	H	D_{OUT}	I_{CC}
Write	L	X	L	D_{IN}	I_{CC}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP. *4	MAX.	UNIT
Supply Voltage	V_{CC}		-10	2.7	3.3	3.6	V
Input High Voltage	V_{IH} *1			2.2	-	V_{CC}+0.3	V
Input Low Voltage	V_{IL} *2			- 0.3	-	0.8	V
Input Leakage Current	I_{LI}	$V_{CC} \geqq V_{IN} \geqq V_{SS}$		- 1	-	1	µA
Output Leakage Current	I_{LO}	$V_{CC} \geqq V_{OUT} \geqq V_{SS}$, Output Disabled		- 1	-	1	µA
Output High Voltage	V_{OH}	I_{OH} = -4mA		2.4	-	-	V
Output Low Voltage	V_{OL}	I_{OL} = 8mA		-	-	0.4	V
Average Operating Power Supply Current	I_{CC}	CE# $\leqq$0.2, Others at 0.2V or Vcc-0.2V $I_{I/O}$ = 0mA;f=max	-10	-	80	110	mA
Standby Power Supply Current	I_{SB1}	CE# $\geqq V_{CC}$ - 0.2V, Others at 0.2V or V_{CC} - 0.2V		-	4	40	mA

Notes:
1. V_{IH}(max) = V_{CC} + 2.0V for pulse width less than 6ns.
2. V_{IL}(min) = V_{SS} - 2.0V for pulse width less than 6ns.
3. Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.
4. Typical values are included for reference only and are not guaranteed or tested.
   Typical valued are measured at V_{CC} = V_{CC}(TYP.) and T_A = 25℃

CAPACITANCE (T_A = 25℃, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Speed	10ns
Input Pulse Levels	0.2V to V_{CC} - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	V_{CC}/2
Output Load	C_L = 30pF + 1TTL, I_{OH}/I_{OL} = -4mA/8mA

AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

PARAMETER	SYM.	AS7C38096B-10		UNIT
		MIN.	MAX.	
Read Cycle Time	t_{RC}	10	-	ns
Address Access Time	t_{AA}	-	10	ns
Chip Enable Access Time	t_{ACE}	-	10	ns
Output Enable Access Time	t_{OE}	-	4.5	ns
Chip Enable to Output in Low-Z	t_{CLZ}*	2	-	ns
Output Enable to Output in Low-Z	t_{OLZ}*	0	-	ns
Chip Disable to Output in High-Z	t_{CHZ}*	-	4	ns
Output Disable to Output in High-Z	t_{OHZ}*	-	4	ns
Output Hold from Address Change	t_{OH}	2	-	ns

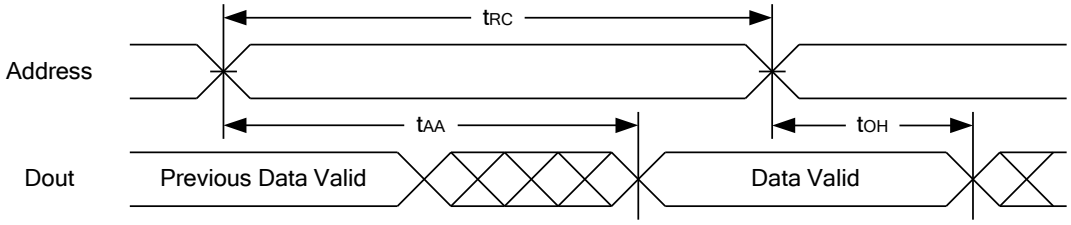
(2) WRITE CYCLE

PARAMETER	SYM.	AS7C38096B-10		UNIT
		MIN.	MAX.	
Write Cycle Time	t_{WC}	10	-	ns
Address Valid to End of Write	t_{AW}	8	-	ns
Chip Enable to End of Write	t_{CW}	8	-	ns
Address Set-up Time	t_{AS}	0	-	ns
Write Pulse Width	t_{WP}	8	-	ns
Write Recovery Time	t_{WR}	0	-	ns
Data to Write Time Overlap	t_{DW}	6	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	ns
Output Active from End of Write	t_{OW}*	2	-	ns
Write to Output in High-Z	t_{WHZ}*	-	4	ns

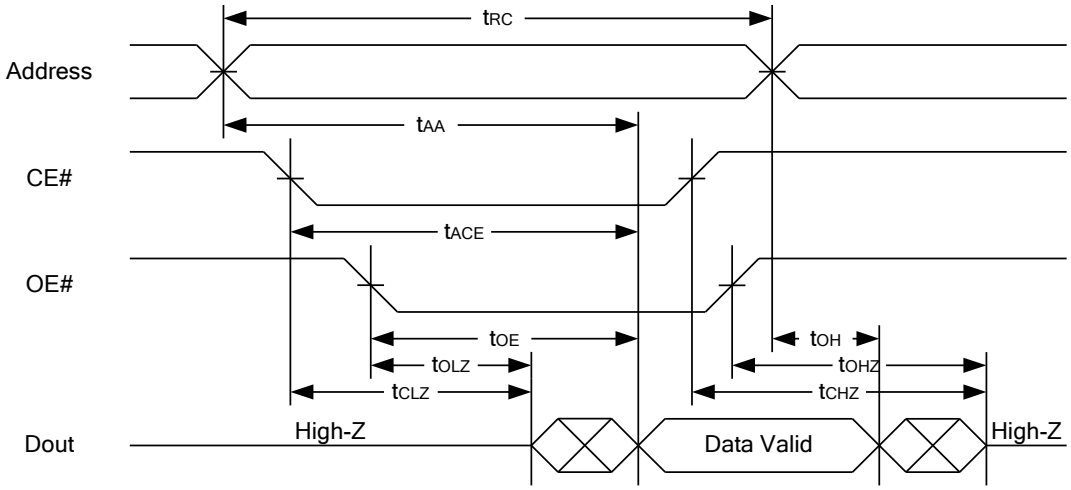
*These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)

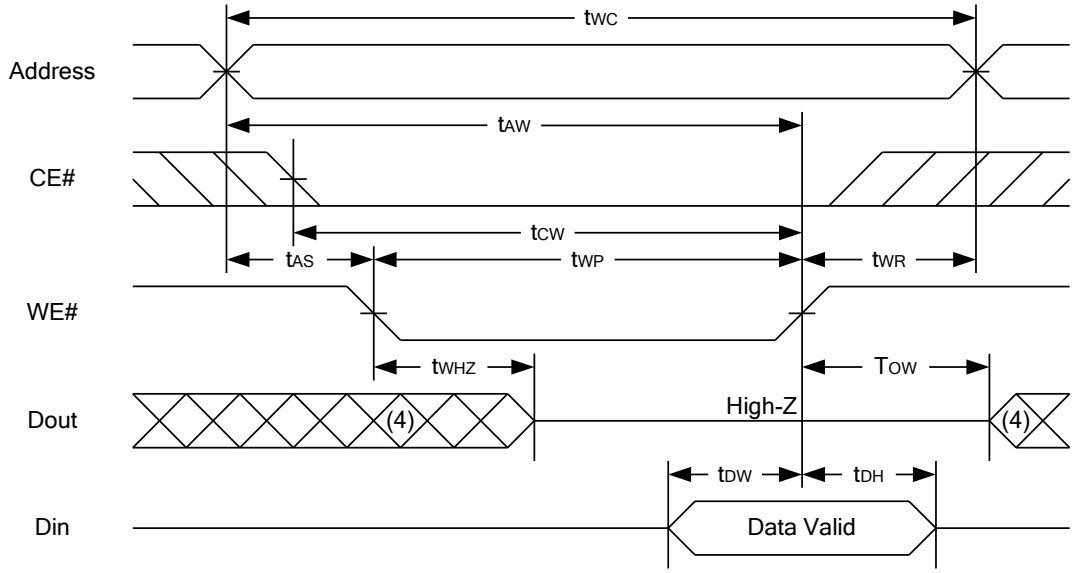


READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)

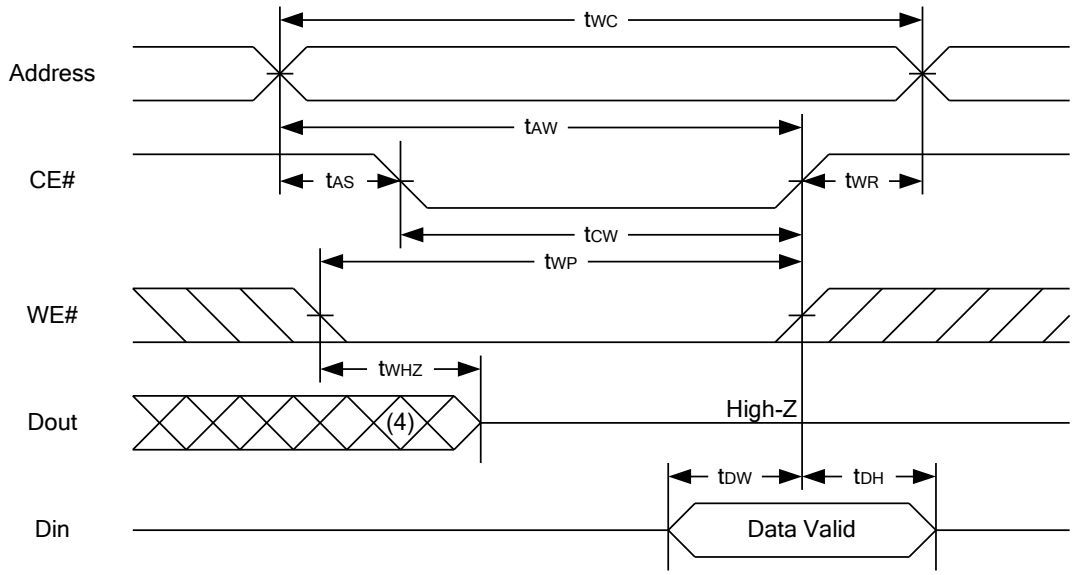


Notes :
1.WE# is high for read cycle.
2.Device is continuously selected OE# = low, CE# = low.
3.Address must be valid prior to or coincident with CE# = low,; otherwise t_{AA} is the limiting parameter.
4.t_{CLZ}, t_{OLZ}, t_{CHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ±500mV from steady state.
5.At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ}.

WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)



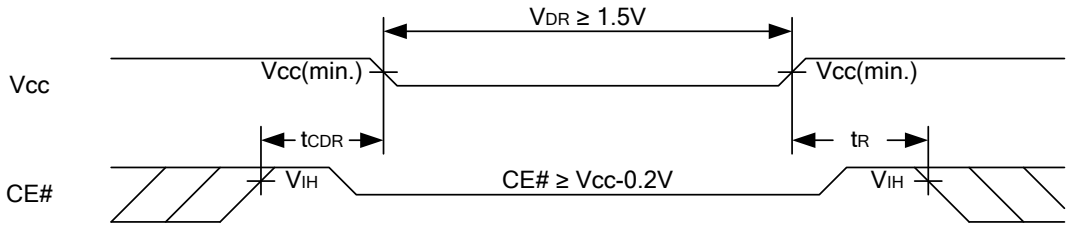
Notes :
1.WE#,CE#, LB#, UB# must be high during all address transitions.
2.A write occurs during the overlap of a low CE#, low WE#, LB# or UB# = low.
3.During a WE# controlled write cycle with OE# low, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
4.During this period, I/O pins are in the output state, and input signals must not be applied.
5.If the CE#, LB#, UB# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
6.t_{OW} and t_{WHZ} are specified with C_L = 5pF. Transition is measured ±500mV from steady state.

DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V_{CC} for Data Retention	V_{DR}	CE# ≧ V_{CC} - 0.2V	1.5	-	3.6	V
Data Retention Current	I_{DR}	V_{CC} = 1.5V CE# ≧ V_{CC} - 0.2V Others at 0.2V or V_{CC} – 0.2V	-	3	25	mA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t_R		t_{RC*}	-	-	ns

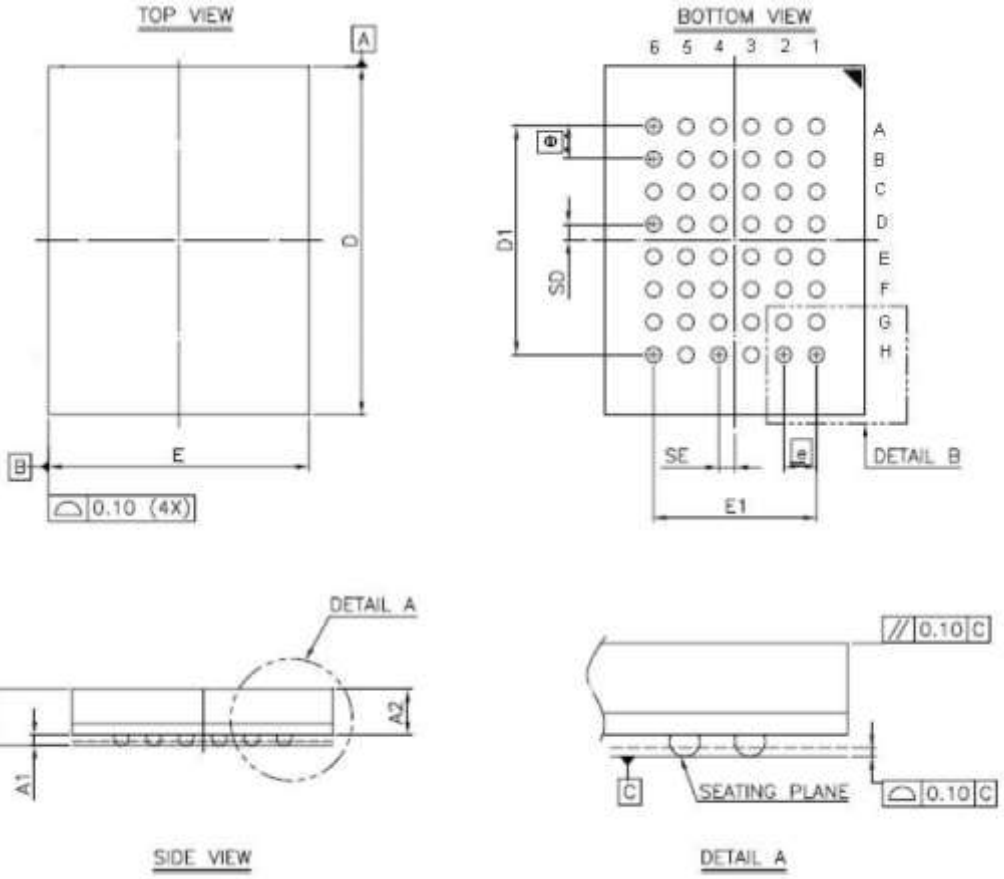
t_{RC*} = Read Cycle Time

DATA RETENTION WAVEFORM

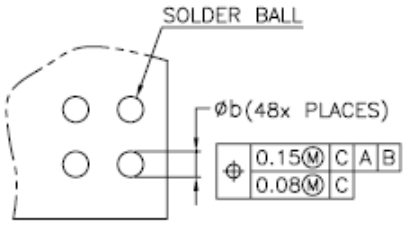


PACKAGE OUTLINE DIMENSION

48-ball 6mm × 8mm TFBGA Package Outline Dimension



SYM.	DIMENSION (mm)			DIMENSION (inch)		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	—	1.40	—	—	0.055
A1	0.20	0.25	0.30	0.008	0.010	0.012
A2	—	—	1.05	—	—	0.041
b	0.30	0.35	0.40	0.012	0.014	0.016
D	7.95	8.00	8.05	0.313	0.315	0.317
D1	5.25 BSC			0.207 BSC		
E	5.95	6.00	6.05	0.234	0.236	0.238
E1	3.75 BSC			0.148 BSC		
SE	0.375 TYP			0.015 TYP		
SD	0.375 TYP			0.015 TYP		
e	0.75 BSC			0.030 BSC		



DETAIL B

NOTE:
1. CONTROLLING DIMENSION : MILLIMETER.
2. REFERENCE DOCUMENT : JEDEC MO-207.

Alliance Memory, Inc., 551 Taylor Way, Suite #1, San Carlos, CA 94070, USA
Tel: +1 650 610 6800 Fax: +1 650 620 9211